

MOSFET – Power, P-Channel, SOIC-8

-30 V, -11.4 A

NTMS4177P

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- SOIC-8 Surface Mount Package Saves Board Space
- This is a Pb-Free Device

Applications

- Load Switches
- Notebook PC's
- Desktop PC's

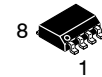
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Symbol	Rating	Value	Unit
V_{DSS}	Drain-to-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$	-8.9 -7.1 A
P_D	Power Dissipation $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	1.52 W
I_D	Continuous Drain Current $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$	-6.6 -5.3 A
P_D	Power Dissipation $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	0.84 W
I_D	Continuous Drain Current $R_{\theta JA}$ $t < 10$ s (Note 1)	$T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$	-11.4 -9.3 A
P_D	Power Dissipation $R_{\theta JA}$ $t < 10$ s (Note 1)	$T_A = 25^\circ\text{C}$	2.5 W
I_{DM}	Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	-46 A
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$
I_S	Source Current (Body Diode)	-2.1	A
EAS	Single Pulse Drain-to-Source Avalanche Energy $T_J = 25^\circ\text{C}$, $V_{DD} = 30$ V, $V_{GS} = 10$ V, $I_L = 20$ A _{pk} , $L = 1.0$ mH, $R_G = 25 \Omega$	200	mJ
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

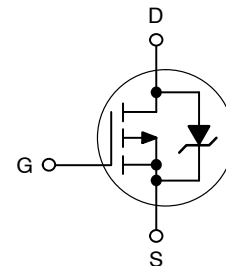
1. Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
-30 V	12 m Ω @ -10 V	-11.4 A
	19 m Ω @ -4.5 V	

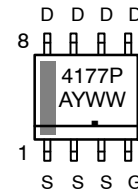


SOIC-8
CASE 751
STYLE 12

P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



4177P = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTMS4177PR2G	SOIC-8 (Pb-Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

NTMS4177P

THERMAL RESISTANCE RATINGS

Symbol	Rating	Max	Unit
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 3)	82	°C/W
$R_{\theta JA}$	Junction-to-Ambient – $t \leq 10$ s (Note 3)	50	
$R_{\theta JF}$	Junction-to-FOOT (Drain)	20	
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 4)	148	

3. Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)jk

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
$V_{(BR)DSS}/T_J$	Drain-to-Source Breakdown Voltage Temperature Coefficient			29		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}$			-1.0	μA
		$T_J = 85^\circ\text{C}$			-5.0	
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-1.5		-2.5	V
$V_{GS(TH)}/T_J$	Negative Threshold Temperature Coefficient			6.0		mV/°C
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = -10\text{ V}, I_D = -11.4\text{ A}$		10	12	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -9.1\text{ A}$		15	19	
g_{FS}	Forward Transconductance	$V_{DS} = -1.5\text{ V}, I_D = -11.4\text{ A}$		30		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

C_{ISS}	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -24\text{ V}$		3100		pF
C_{OSS}	Output Capacitance			550		
C_{RSS}	Reverse Transfer Capacitance			370		
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -11.4\text{ A}$		29		nC
$Q_{G(TH)}$	Threshold Gate Charge			3.3		
Q_{GS}	Gate-to-Source Charge			10		
Q_{GD}	Gate-to-Drain Charge			13		
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}, I_D = -11.4\text{ A}$		55		nC
R_G	Gate Resistance			2.0	4.0	Ω

SWITCHING CHARACTERISTICS (Note 6)

$t_{d(ON)}$	Turn-On Delay Time	$V_{GS} = -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -1.0\text{ A}, R_G = 6.0\text{ }\Omega$		18		ns
t_r	Rise Time			13		
$t_{d(OFF)}$	Turn-Off Delay Time			64		
t_f	Fall Time			36		

DRAIN-TO-SOURCE CHARACTERISTICS

V_{SD}	Forward Diode Voltage	$V_{GS} = 0\text{ V}, I_D = -2.1\text{ A}$	$T_J = 25^\circ\text{C}$		-0.73	-1.0	V
			$T_J = 125^\circ\text{C}$		0.54		
t_{RR}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = -2.1\text{ A}$		34		ns	
T_a	Charge Time			18			
T_b	Discharge Time			16			
Q_{RR}	Reverse Recovery Time			30			nC

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

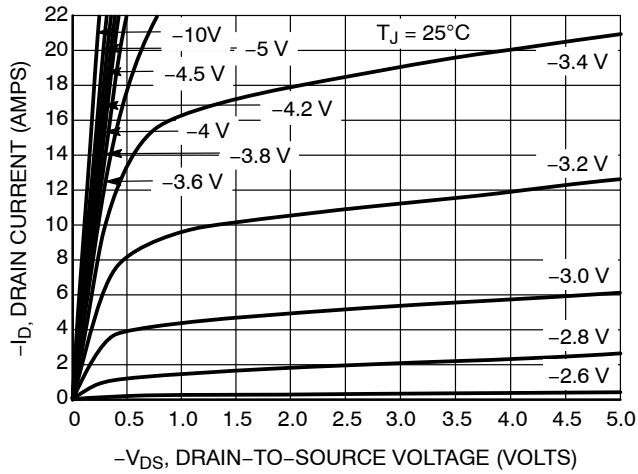


Figure 1. On-Region Characteristics

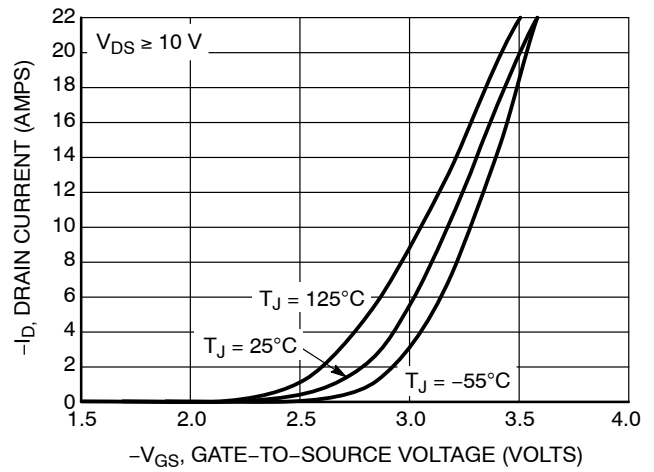


Figure 2. Transfer Characteristics

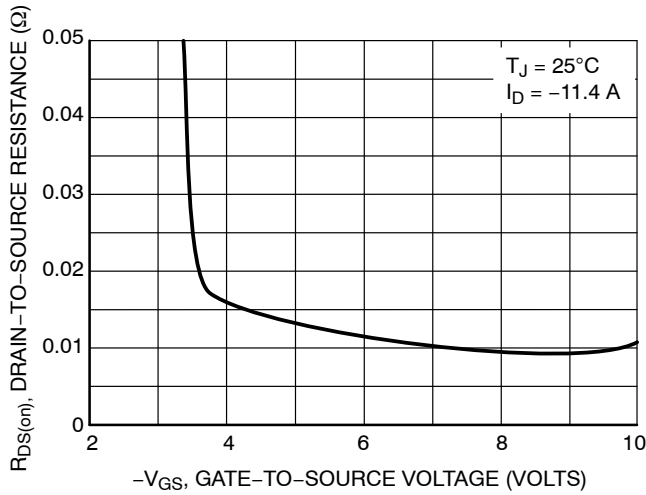


Figure 3. On-Resistance vs. Gate-to-Source Voltage

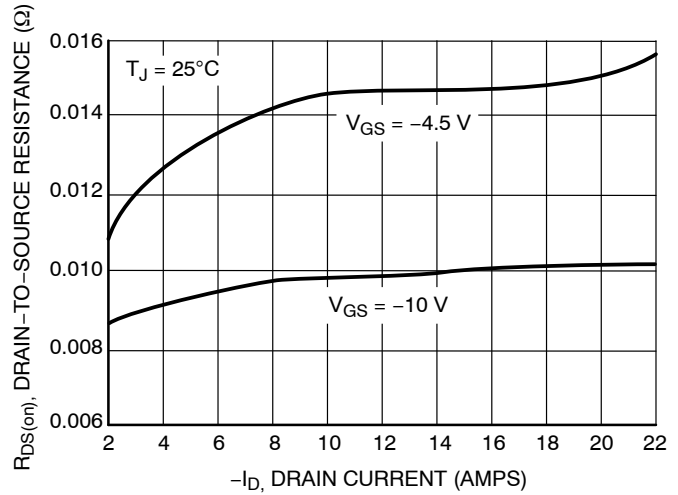


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

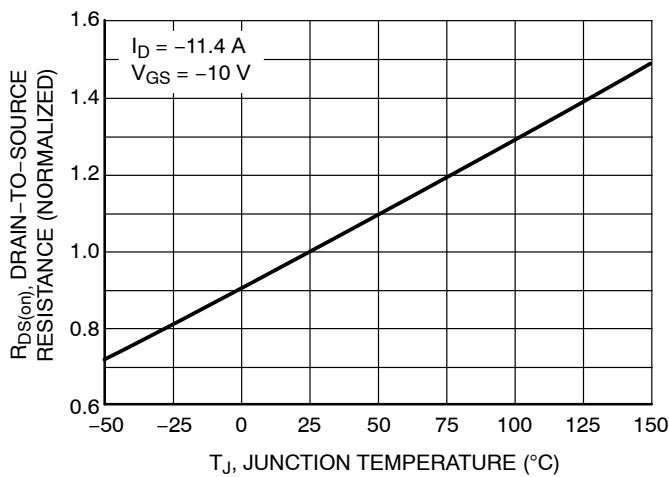


Figure 5. On-Resistance Variation with Temperature

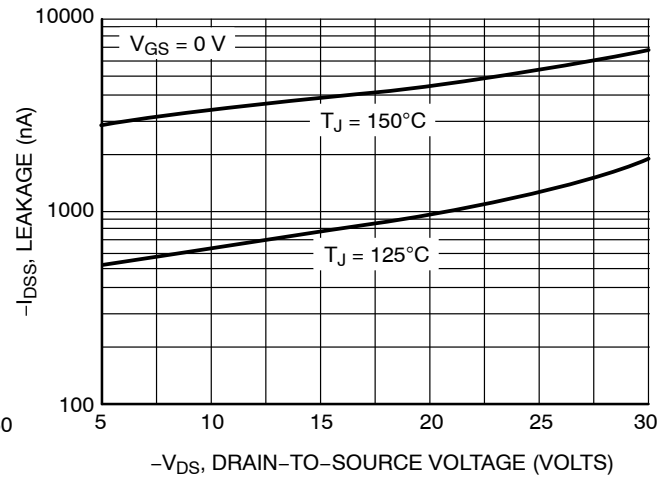


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES (continued)

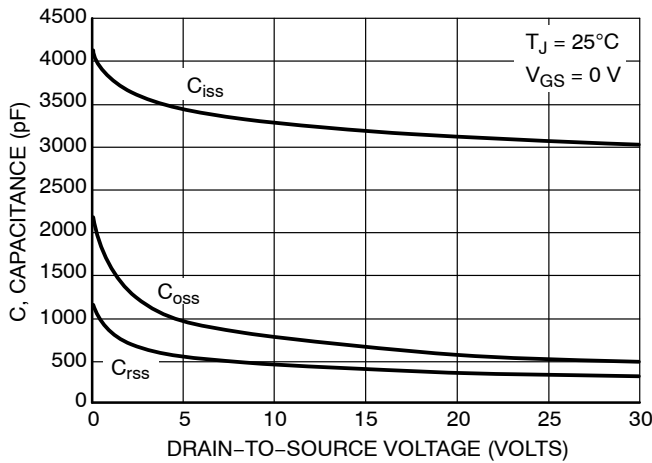


Figure 7. Capacitance Variation

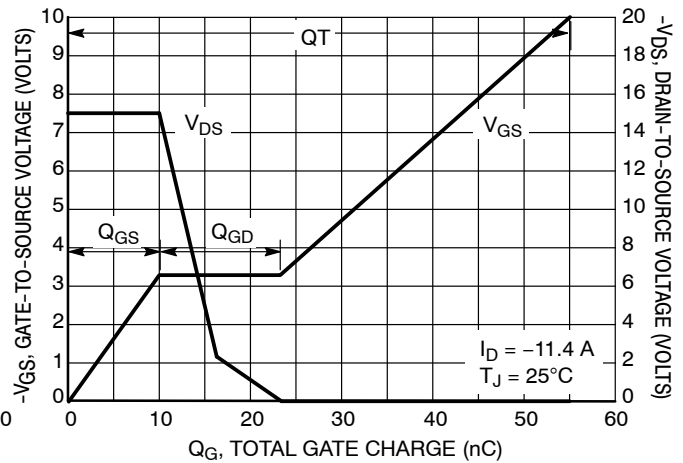


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

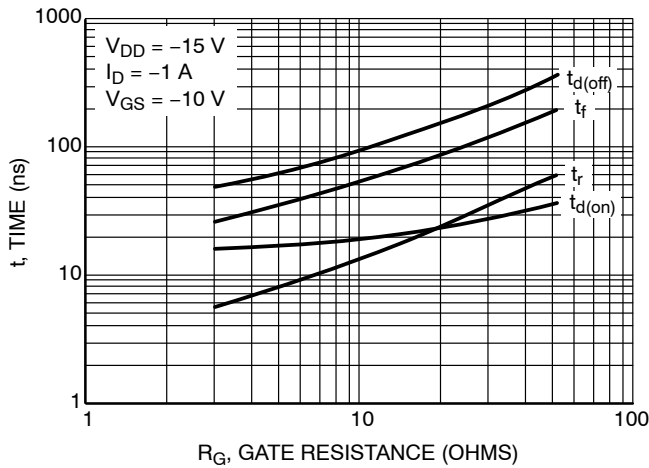


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

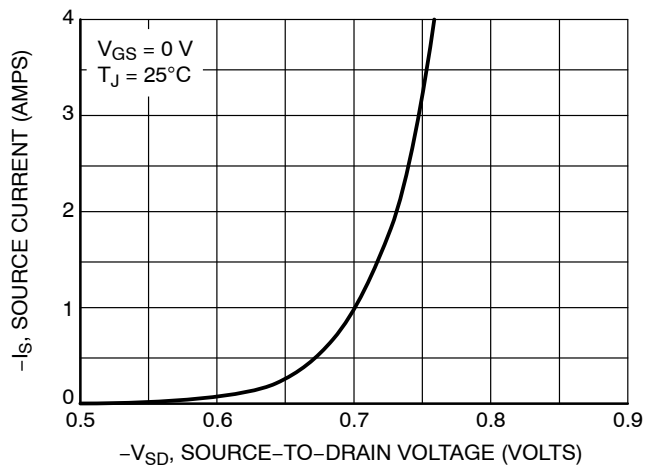


Figure 10. Diode Forward Voltage vs. Current

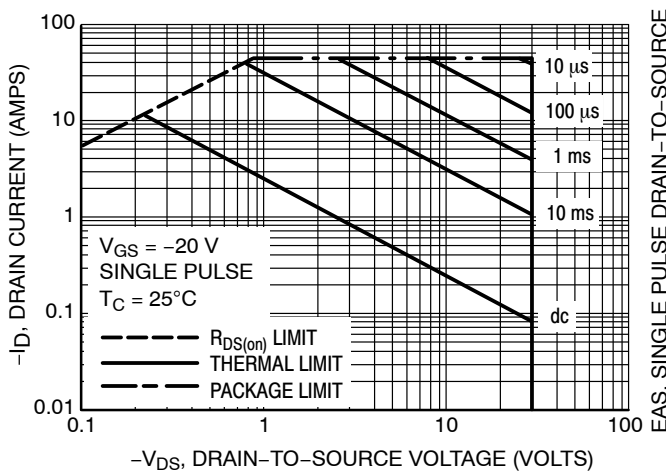


Figure 11. Maximum Rated Forward Biased Safe Operating Area

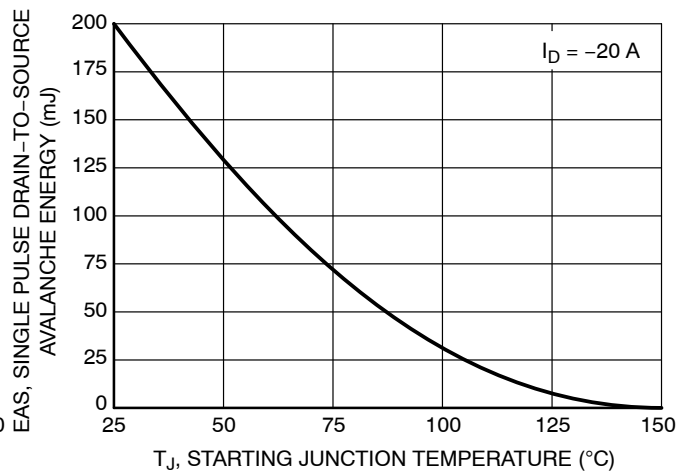


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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